

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 4 A, 650 V, D1, DPAK

FFSD0465A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 25 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

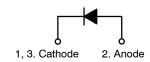
ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Paramete	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		25	mJ
Ι _Ε	Continuous Rectified Forward Current @ T _C < 160°C		4	Α
	Continuous Rectified Forward Current @ T _C < 135°C		7.6	
I _{F, Max}	Non-Repetitive Peak Forward	T _C = 25°C, 10 μs	360	Α
	Surge Current	T _C = 150°C, 10 μs	330	Α
I _{F, SM}	Non-Repetitive Forward Surge Current	Half–Sine Pulse, t _P = 8.3 ms	38	Α
I _{F, RM}	Repetitive Forward Surge Current	Half–Sine Pulse, t _P = 8.3 ms	18	Α
Ptot	Power Dissipation	T _C = 25°C	61	W
		T _C = 150°C	10	W
T _J ,T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 25 mJ is based on starting $T_J = 25^{\circ}C$, $\dot{L} = 0.5$ mH, $I_{AS} = 10$ A, V = 50 V

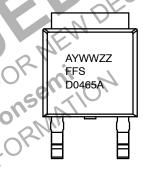
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Schottky Diode



CASE 369AS MARKING DIAGRAM



A ~ YWW ZZ

- = Assembly Plant Code
- = Date Code (Year & Week)
 - = Lot Code
- FFSD0465A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSD0465A

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.	2.46	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 4 A, T _C = 25°C	-	1.50	1.75	V
		I _F = 4 A, T _C = 125°C	-	1.6	2.0	
		I _F = 4 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	-	200	μΑ
		V _R = 650 V, T _C = 125°C	-	-	400	
		V _R = 650 V, T _C = 175°C	-	-	600	
Q _C	Total Capacitive Charge	V = 400 V	-	16	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	258	- 6	p F
		V _R = 200 V, f = 100 kHz	-	29		
		V _R = 400 V, f = 100 kHz	-	21		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package Shipping*
FFSD0465A	FFSD0465A	DPAK 2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

TYPICAL CHARACTERISTICS

(T_{.L} = 25°C UNLESS OTHERWISE NOTED)

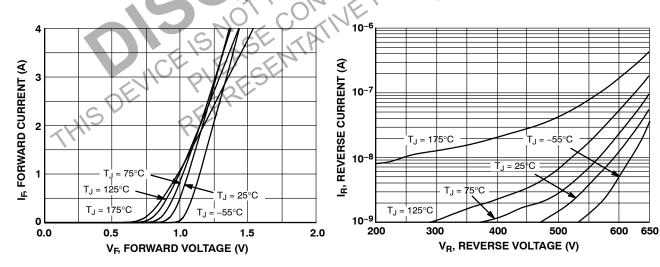


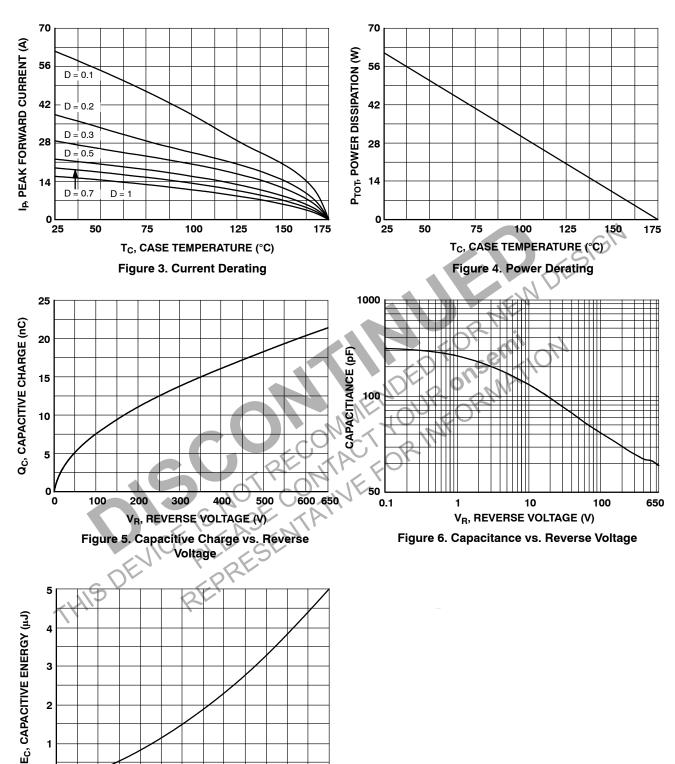
Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics

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TYPICAL CHARACTERISTICS (CONTINUED)

(T_J = 25°C UNLESS OTHERWISE NOTED)



V_R, REVERSE VOLTAGE (V) Figure 7. Capacitance Stored Energy

400

3

100

600 650

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TYPICAL CHARACTERISTICS (CONTINUED)

(T_J = 25°C UNLESS OTHERWISE NOTED)

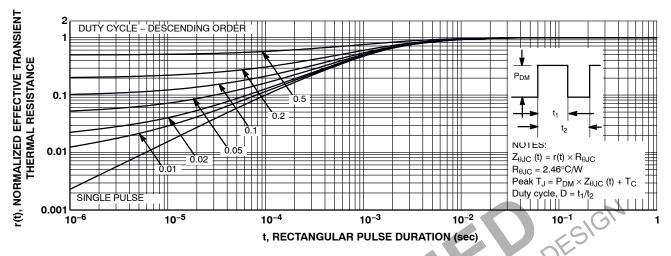


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

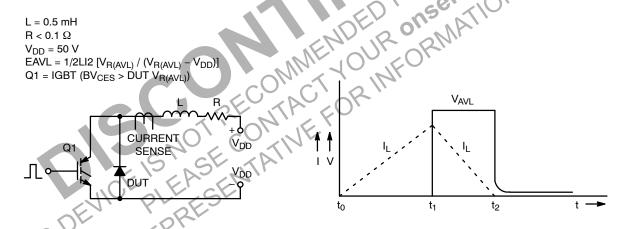


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform





DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS **ISSUE B**

DATE 20 DEC 2023

- NOTES: UNLESS OTHERWISE SPECIFIED

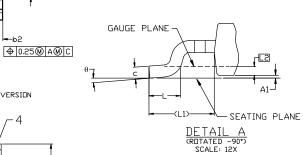
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.

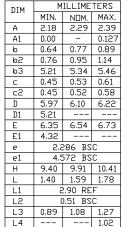
 B) ALL DIMENSIONS ARE IN MILLIMETERS.

 C) DIMENSIONING AND TOLERANCING PER

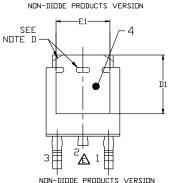
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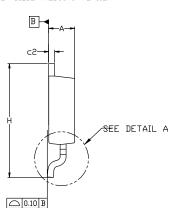
- A
- F)
- DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M-2018.
 SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
 CORNERS OR EDGE PROTRUSION.
 FOR DIGDE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY
 STUB WITHOUT CENTER LEAD.
 DIMENSIONS ARE EXCLUSIVE OF BURRS,
 MOLD FLASH AND TIE BAR EXTRUSIONS.
 LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
 T0228P991X239-3N.

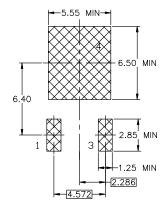




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LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

10°

XXXXXX XXXXXX **AYWWZZ**

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code

= Assembly Location Α

Υ = Year

WW = Work Week

77 = Assembly Lot Code

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